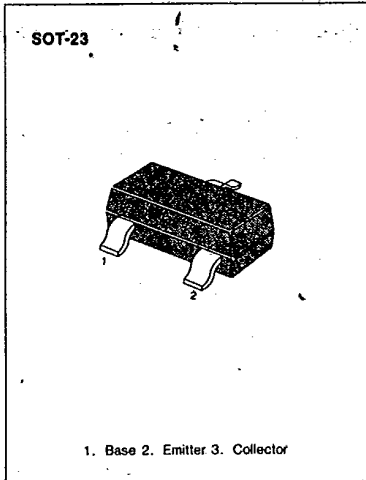


MMBC1009F4 NPN EPITAXIAL SILICON TRANSISTOR

AM/FM RF AMPLIFIER TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	25	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	50	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 15V, I _E = 0			100	nA
DC Current Gain	h _{FE}	V _{CE} = 3V, I _C = 0.5mA	90		180	
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = 10mA, I _B = 1.0mA			0.3	V
Current Gain-Bandwidth Product	f _T	I _C = 1mA, V _{CE} = 6V f = 100MHz	150			MHz
Output Capacitance	C _{ob}	V _{CB} = 6V, I _E = 0 f = 1MHz		2		pF
Noise Figure	NF	I _C = 0.5mA, V _{CE} = 6V f = 1MHz, R _g = 500Ω		2.5		dB

Marking

